

POWER SCHOTTKY RECTIFIER

Table 1: Main Product Characteristics

$I_{F(AV)}$	1 A
V_{RRM}	20 V
$T_j(\text{max})$	150°C
$V_F(\text{max})$	0.41 V

FEATURES AND BENEFITS

- Very small conduction losses
- Negligible switching losses
- Extremely fast switching
- Low forward voltage drop for higher efficiency and extended battery life
- Low thermal resistance
- Avalanche capability specified

DESCRIPTION

Single Schottky rectifier suited for switch mode power supplies and high frequency DC to DC converters.

Packaged in STmite, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications. Due to the small size of the package this device fits battery powered equipment (cellular, notebook, PDA's, printers) as well chargers and PCMCIA cards.

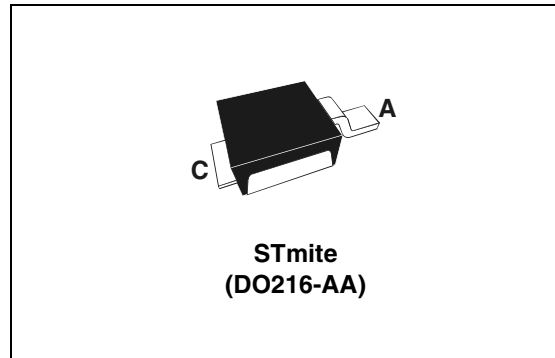


Table 2: Order Code

Part Number	Marking
STPS120M	120

Table 3: Absolute Ratings (limiting values)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	20	V
$I_{F(RMS)}$	RMS forward current	2	A
$I_{F(AV)}$	Average forward current	$T_c = 140^\circ\text{C} \quad \delta = 0.5$ 1	A
I_{FSM}	Surge non repetitive forward current	$t_p = 8.3 \text{ ms sinusoidal}$ 50	A
P_{ARM}	Repetitive peak avalanche power	$t_p = 1 \mu\text{s} \quad T_j = 25^\circ\text{C}$ 1400	W
T_{stg}	Storage temperature range	-65 to + 150	°C
T_j	Maximum operating junction temperature *	150	°C
dV/dt	Critical rate of rise of reverse voltage (rated V_R , $T_j = 25^\circ\text{C}$)	10000	V/ μs

*: $\frac{dP_{tot}}{dT_j} > \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink

STPS120M

Table 4: Thermal Resistance

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$ *	Junction to case	20	°C/W
$R_{th(j-l)}$ *	Junction to ambient	250	°C/W

* Mounted with minimum recommended pad size, PC board FR4.

Table 5: Static Electrical Characteristics

Symbol	Parameter	Tests conditions	Min.	Typ	Max.	Unit
I_R *	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$	1.3	3.9	μA
		$T_j = 100^\circ\text{C}$		275	850	
		$T_j = 25^\circ\text{C}$	$V_R = 10\text{V}$	0.6	2.0	
		$T_j = 100^\circ\text{C}$		145	450	
		$T_j = 25^\circ\text{C}$	$V_R = 5\text{V}$	0.4	1.0	
		$T_j = 100^\circ\text{C}$		105	300	
V_F *	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 1\text{A}$	0.44	0.49	V
		$T_j = 100^\circ\text{C}$		0.36	0.41	
		$T_j = 25^\circ\text{C}$	$I_F = 3\text{A}$	0.48	0.54	
		$T_j = 100^\circ\text{C}$		0.42	0.48	

Pulse test: * $t_p = 380 \mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation: $P = 0.34 \times I_{F(AV)} + 0.07 I_{F(RMS)}^2$

Figure 1: Conduction losses versus average current

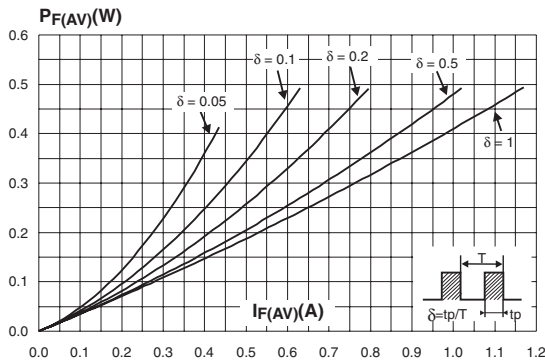


Figure 2: Average forward current versus ambient temperature ($\delta = 0.5$)

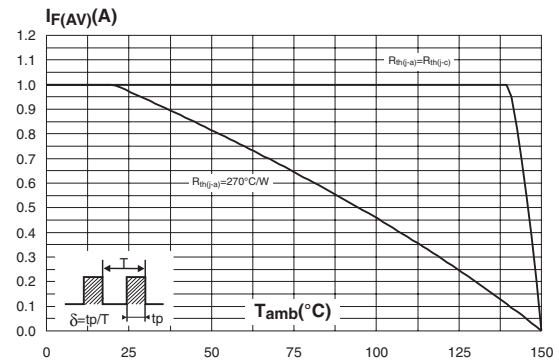


Figure 3: Normalized avalanche power derating versus pulse duration

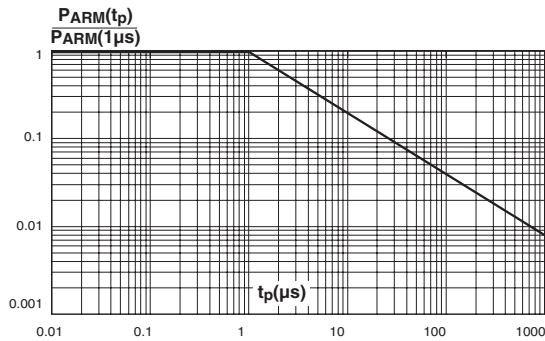


Figure 4: Normalized avalanche power derating versus junction temperature

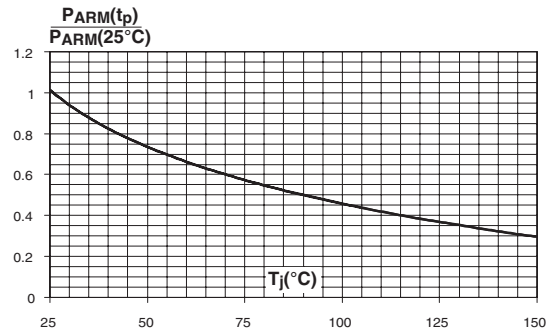


Figure 5: Non repetitive surge peak forward current versus overload duration (maximum values)

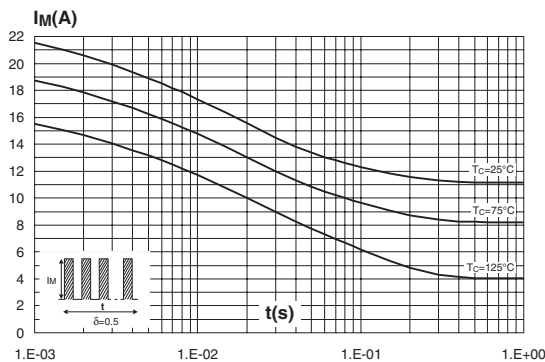


Figure 6: Relative variation of thermal impedance junction to ambient versus pulse duration

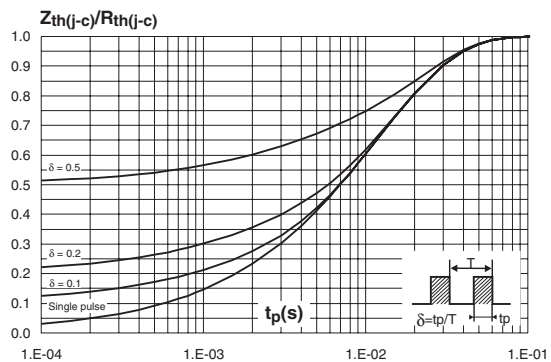


Figure 7: Reverse leakage current versus reverse voltage applied (typical values)

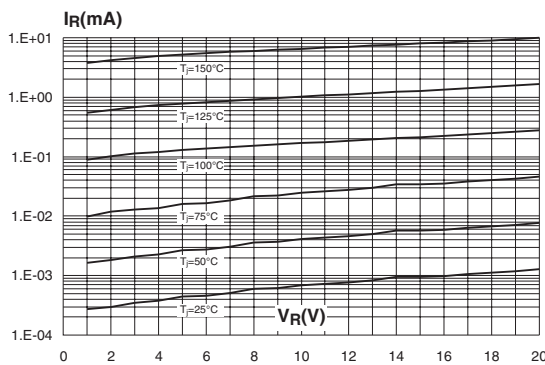


Figure 8: Junction capacitance versus reverse voltage applied (typical values)

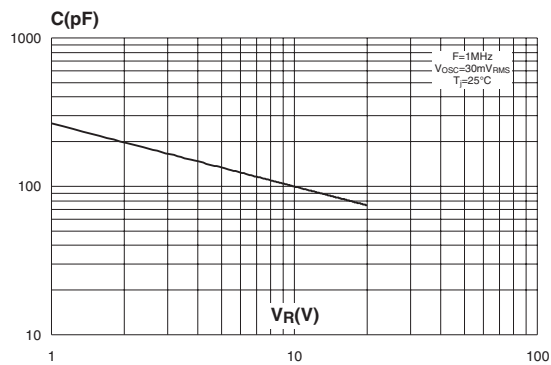


Figure 9: Forward voltage drop versus forward current (low level)

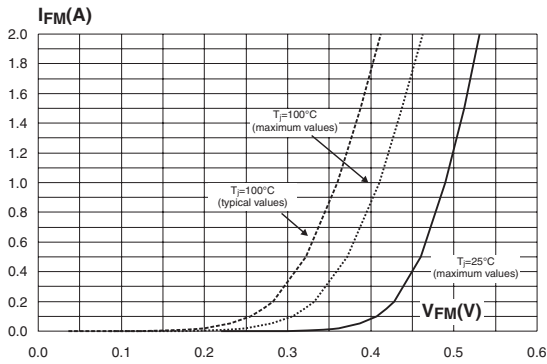


Figure 10: Forward voltage drop versus forward current (high level)

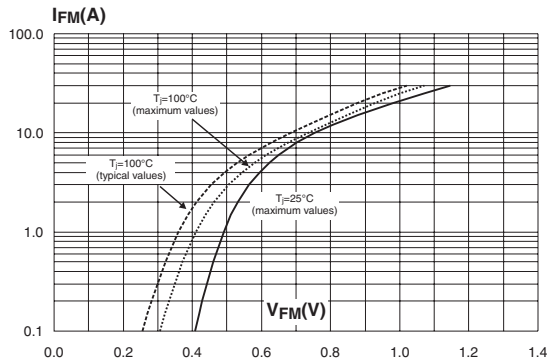


Figure 11: Thermal resistance junction to ambient versus copper surface under tab (epoxy printed board FR4, Cu = 35 μm , typical values)

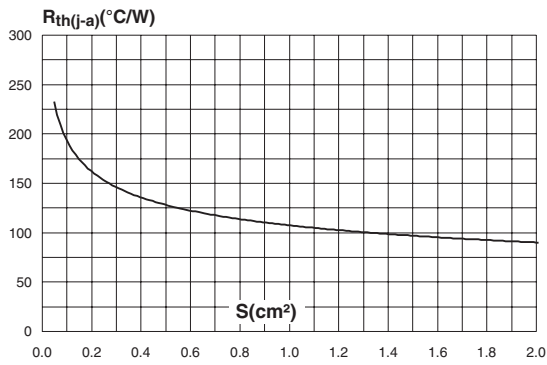


Figure 12: STmite Package Mechanical Data

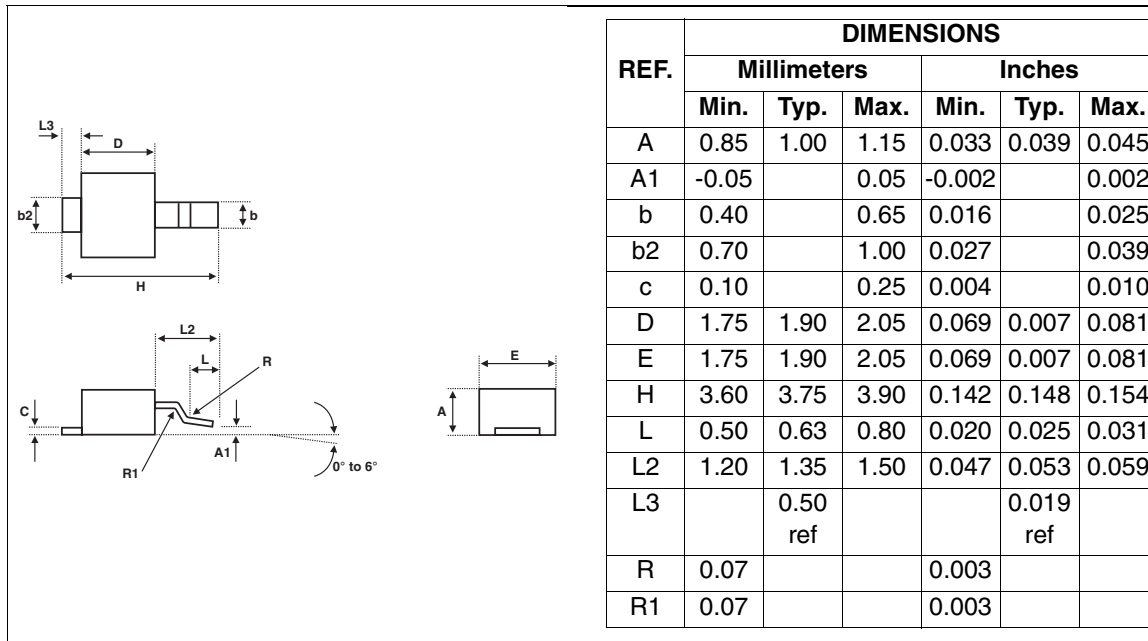


Figure 13: Foot Print Dimensions (in millimeters)

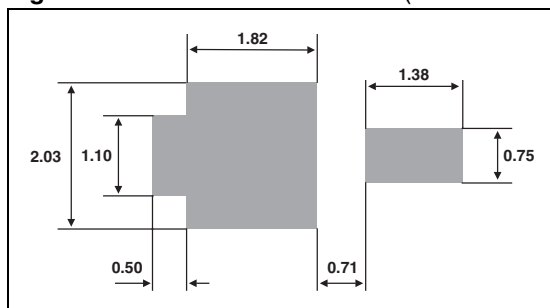


Table 6: Ordering Information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS120M	120	STmite	15.5 mg	12000	Tape & reel

Table 7: Revision History

Date	Revision	Description of Changes
Jul-2003	2A	Last update.
13-Sep-2004	3	STmite package dimensions reference A1 change: from blank (min) to -0.05mm and from 0.10 (max) to 0.05mm.

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